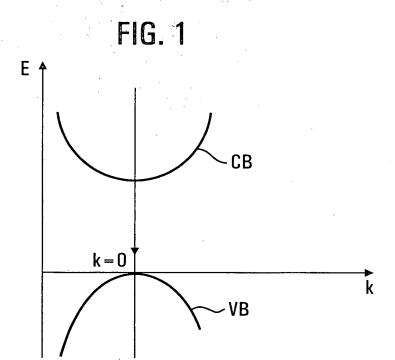
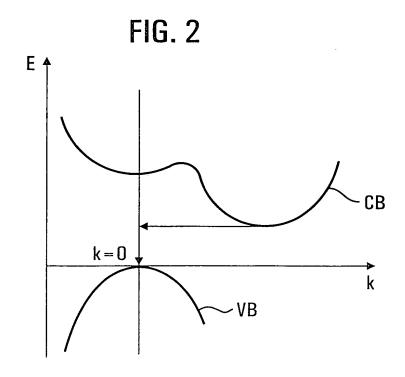
Page 1 of 10

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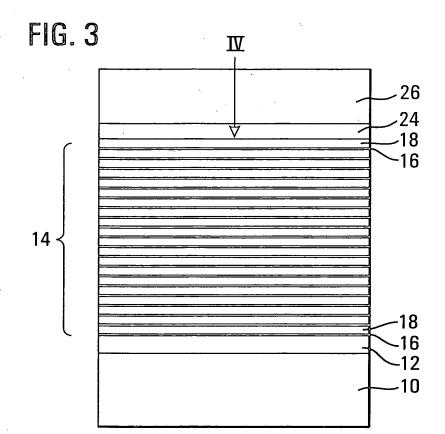


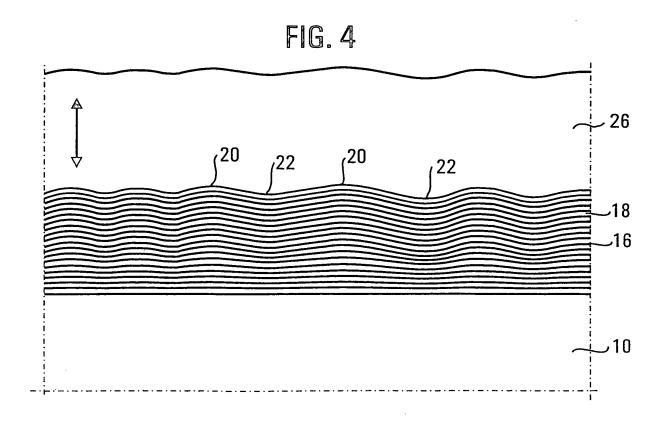


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Page 2 of 10

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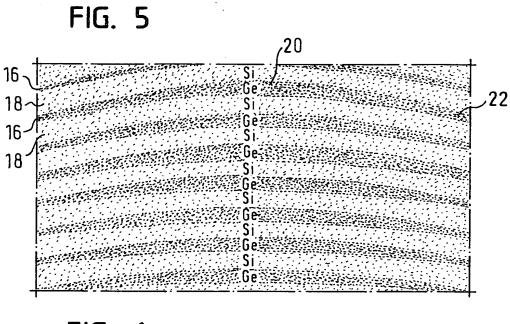


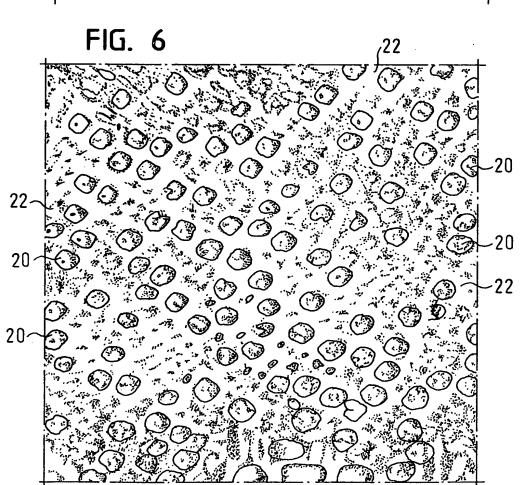
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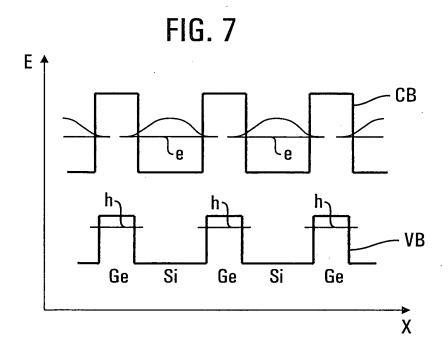


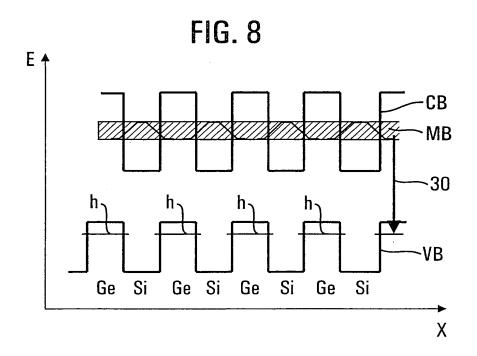
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Page 4 of 10

Attorney: William P. Wilbar Sierra Patent Group, Ltd. Response to Office Action

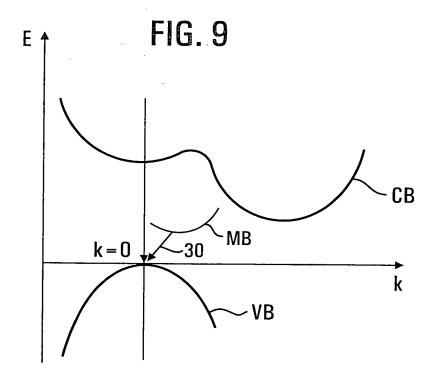


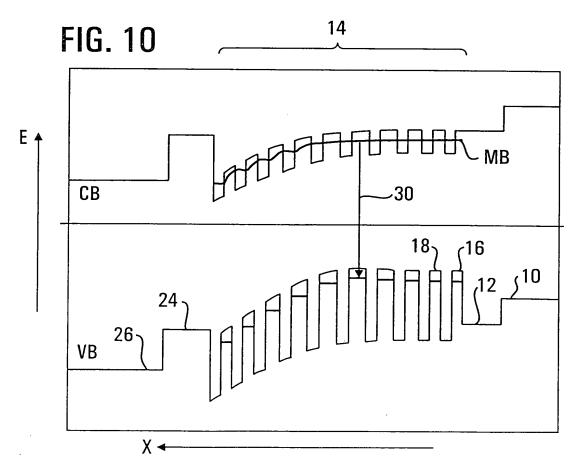


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Submitted on April 29, 2005 with Response to Office Action





Page 6 of 10

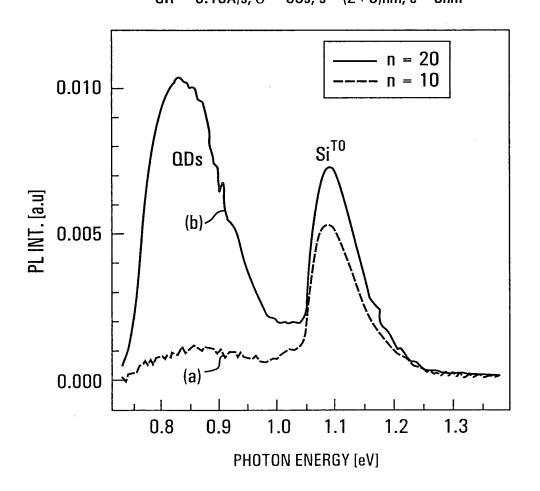
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FIG. 11

PL vs NUMBER OF LAYERS (n) T=300~K $E_{exc}=2.54eV,\,P=5W/cm^2$ $GR=0.15A/s,\,\delta=30s,\,s=(2+3)nm,\,c=5nm$



Page 7 of 10

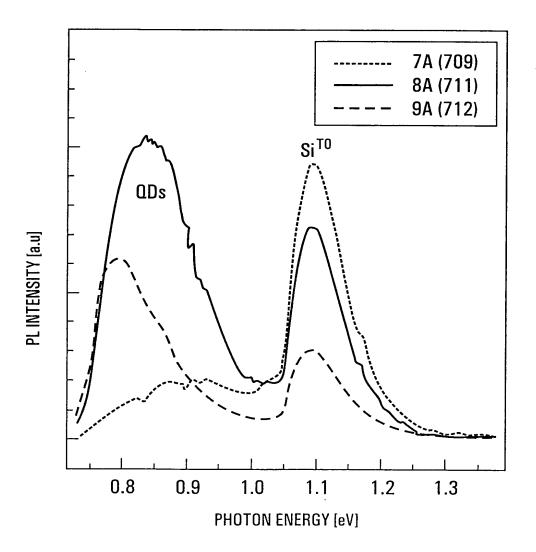
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FIG. 12

PL vs Ge THICKNESS (d) T = 300K $E_{exc} = 2.54 eV, P = 5W/cm^2$ GR = 0.15 A/s, c = 5nm



Serial No.: 10/723,285 Inventors: Werner et al. Filed: November 25, 2003 Title: SEMICONDUCTOR STRUCTURE FOR USE IN THE NEAR INFRARED REGION AND A METHOD OF MANUFACTURING THIS SEMICONDUCTOR STRUCTURE Attorney: William P. Wilbar REPLACEMENT SHEET

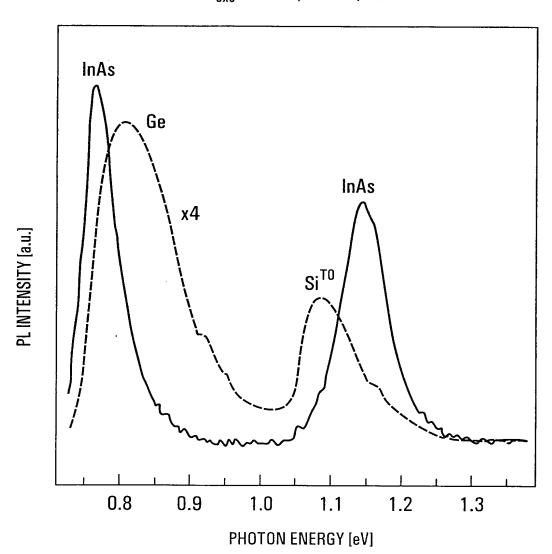
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Docket No.: MAN-013 Page 8 of 10

FIG. 13

Ge-QDs vs InAs-QDs [LTLS] PL at T = 300K E_{exc} = 2.54eV, P = 1W/cm²

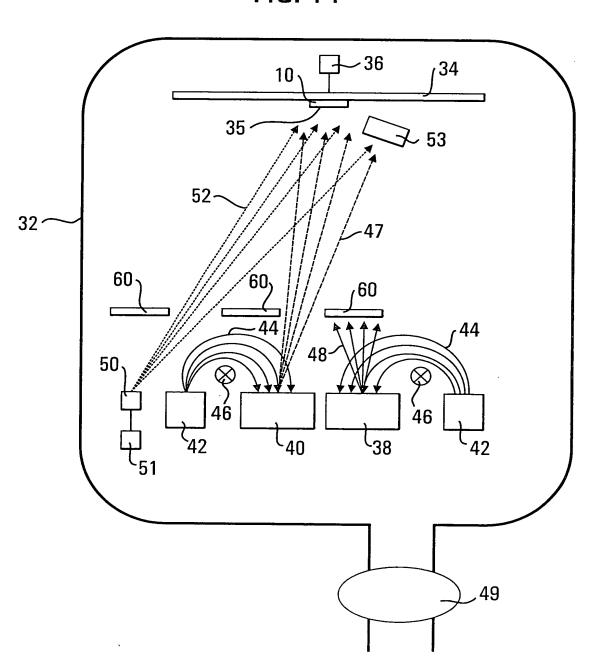


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FIG. 14



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Page 10 of 10

